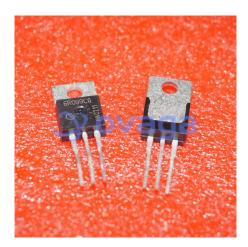


IPP60R099C6

Data Sheet

N-Channel MOSFETs (>500V...900V); Package: PG-TO220-3; VDS (max): 600.0 V; Package: TO-220; RDS(ON) @ TJ=25°C VGS=10: 99.0 mOhm; ID(max) @ TC=25°C: 38.0 A; IDpuls (max): 112.0 A;

Manufacturers	Infineon Technologies Corporation
Package/Case	TO-220
Product Type	Transistors
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for IPP60R099C6 or Email to us: sales@ovaga.com We will contact you in 12 hours.
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General Description

IPP60R099C6 is a power MOSFET transistor manufactured by Infineon Technologies. It is part of the CoolMOS C6 series and is designed for use in high power switching applications.

Features

Low on-state resistance (RDS(on)) of 0.099 Ohms

High switching speed

Low gate charge

Avalanche rated

High reliability and ruggedness

Halogen-free and RoHS compliant

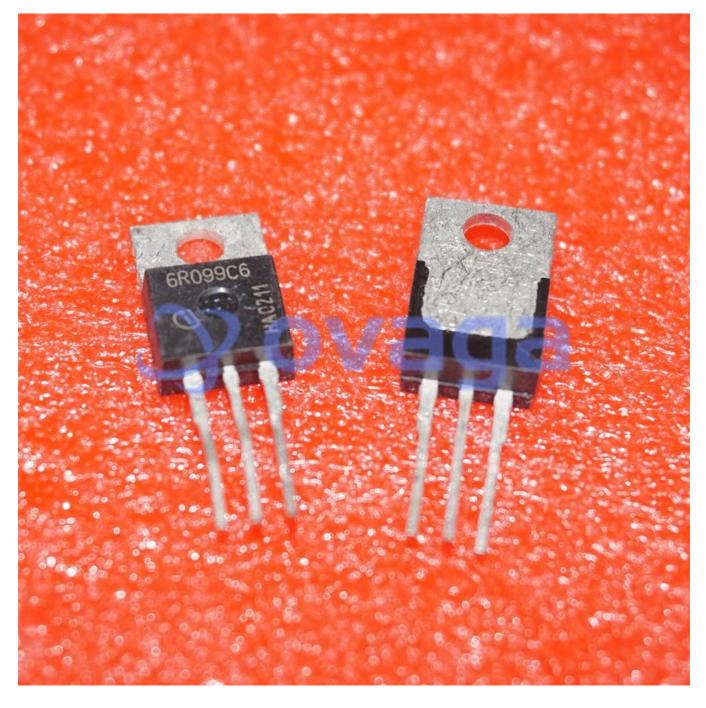
Application

STMicroelectronics STW62N65M5

Nexperia PSMN2R0-60YS

Vishay Siliconix SiHF60N50E

ON Semiconductor FCPF60N60E



Related Products



IPP60R070CFD7

Infineon Technologies Corporation TO-220-3



IPG20N04S4-12

Infineon Technologies Corporation TDSON-8



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IPB180N06S4-H1

Infineon Technologies Corporation PG-TO263-7-3

IPW65R080CFD

Infineon Technologies Corporation TO-247



IPD25N06S4L-30

Infineon Technologies Corporation PG-TO252-3



IPD180N10N3G

Infineon Technologies Corporation TO-252



IPP60R074C6

Infineon Technologies Corporation TO-220-3



IPD70R1K4P7S

Infineon Technologies Corporation TO252-3